

Heterostructure Materials for Photon Enhanced Thermionic Emission and Micro-Thermionics

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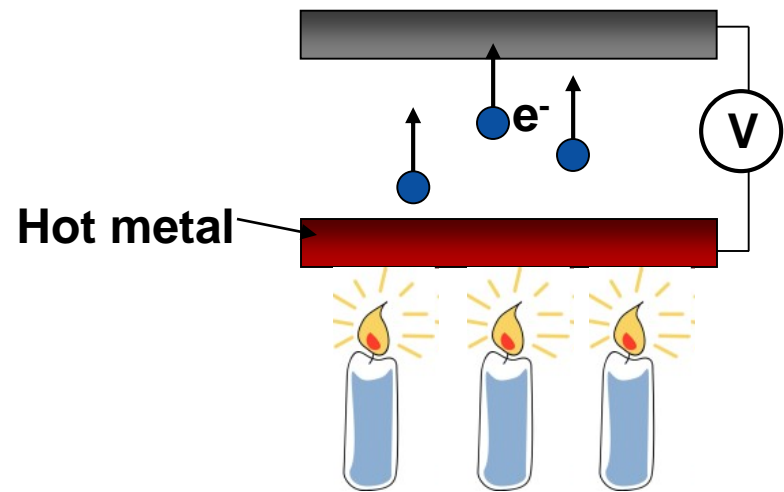
Thermionic Emission

Boiling water:



- Input heat energy to overcome energy barrier to change liquid into gas

Boiling electrons from a metal:



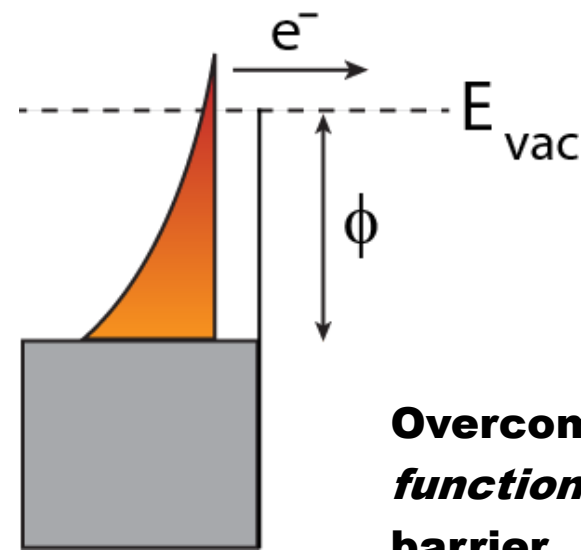
- Operates at very high temperatures; generally $>800^{\circ}\text{C}$

- Robust

$$J = AT^2 e^{-\Phi_E / kT}$$

(Richardson-Dushman law)

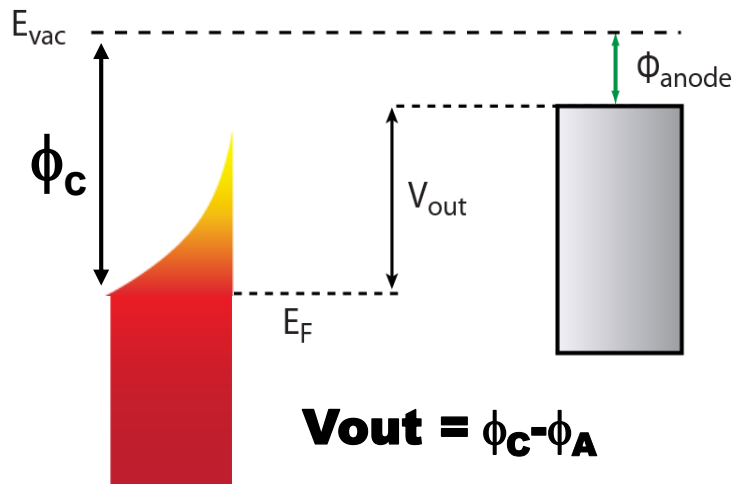
J = current density (Acm^{-2}),
 Φ_E = emitter work function (eV)



Overcome work-function energy barrier

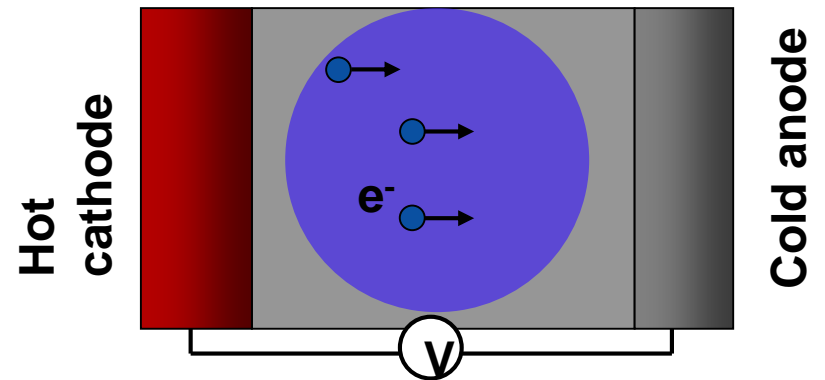
Two Key problems with TEC:

High-T / Low V_{out}



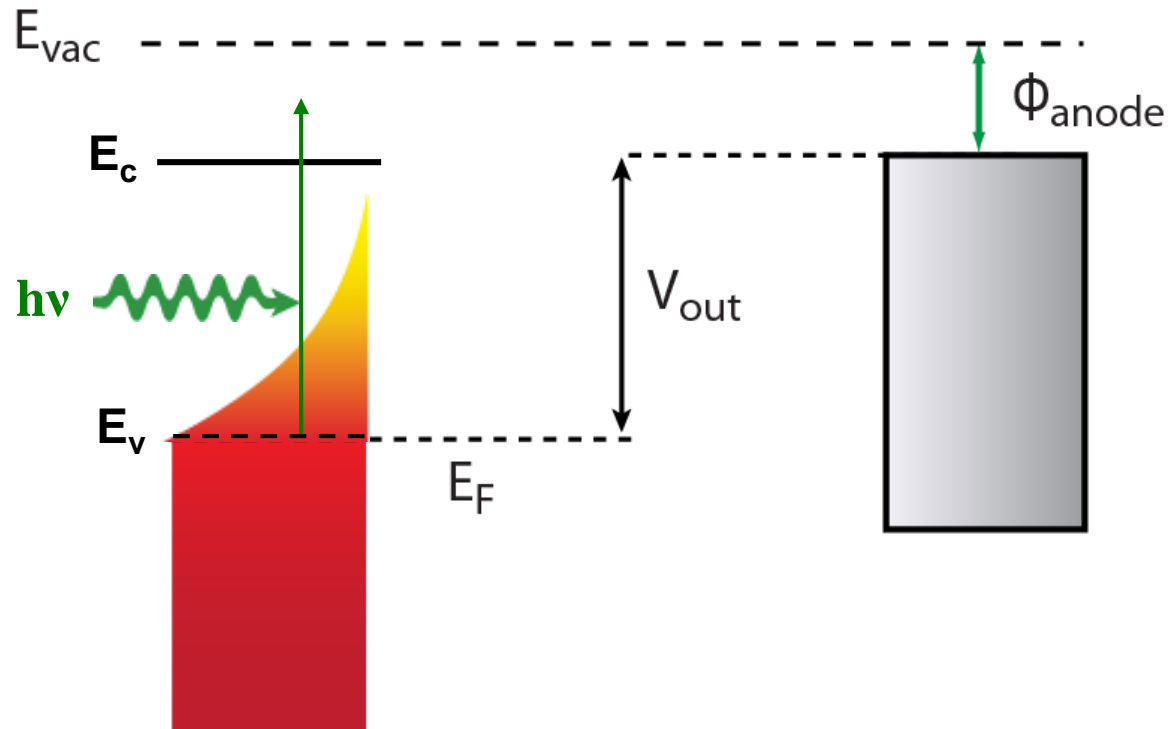
- need reasonable cathode ϕ_C to have decent voltage
- Need high temperature ($>1200C$) to overcome workfunction
- Still need small anode ϕ_A

Space Charge



- Electrons take time to cross vacuum gap
- Electric field builds up, decreasing electron emission
- Current saturation given by Child-Langmuir equation

The PETE Process

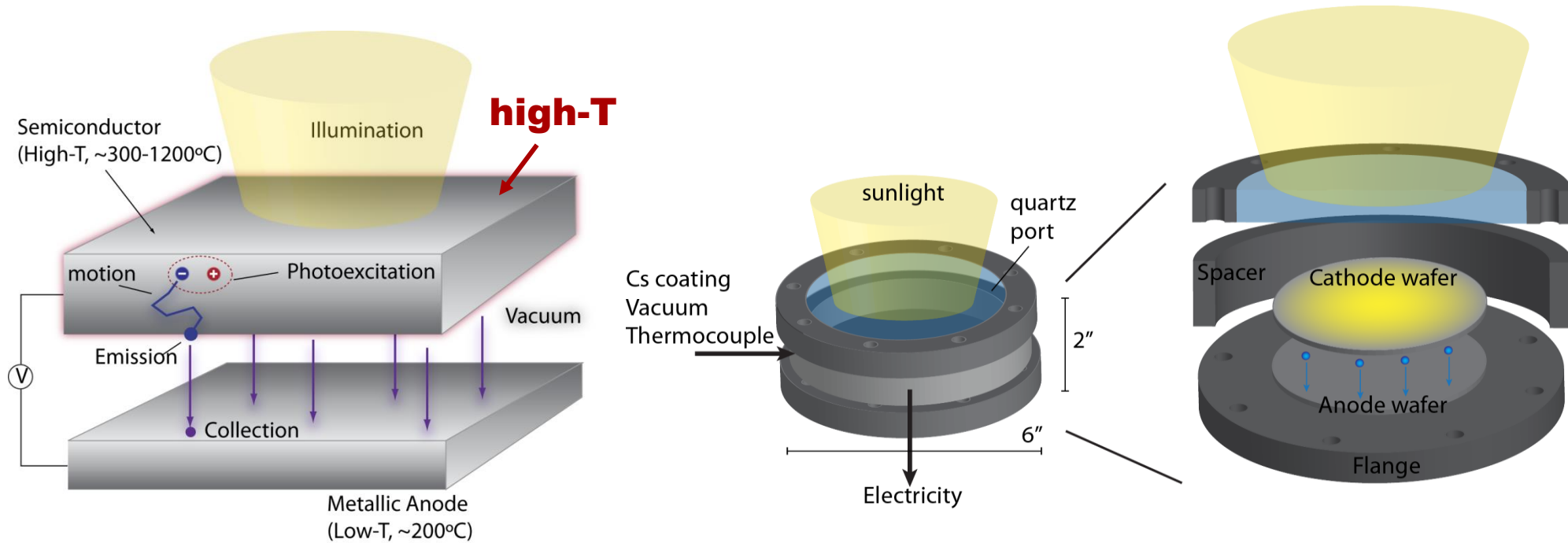


semiconductor

Photon-enhanced Thermionic Emission (PETE)

- **Acts like a high-T PV cell: direct solar to electrical generation at high-T**

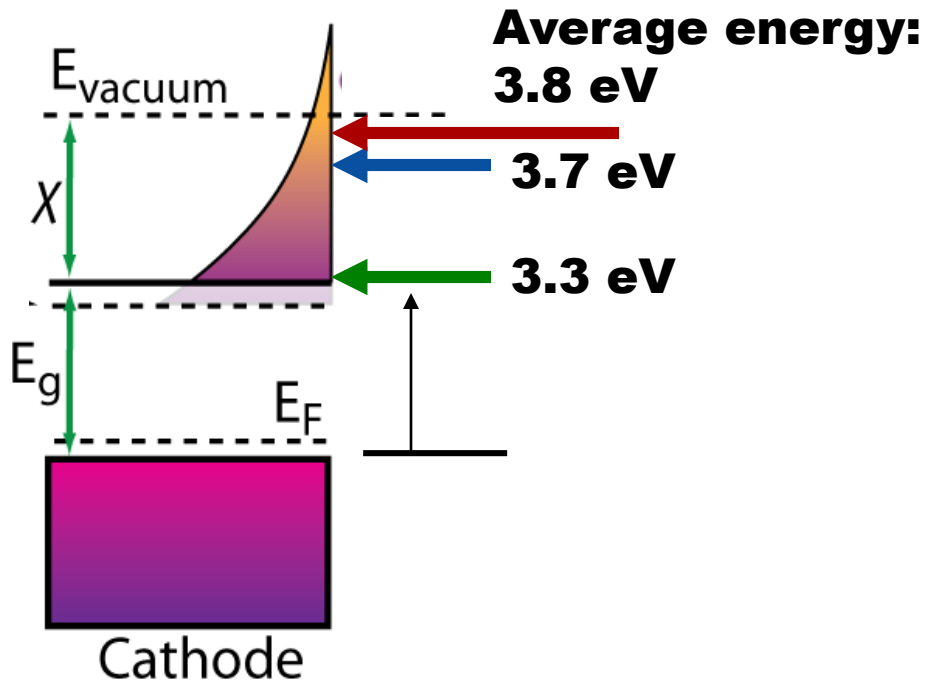
Photon Enhanced Thermionic Emission (PETE)



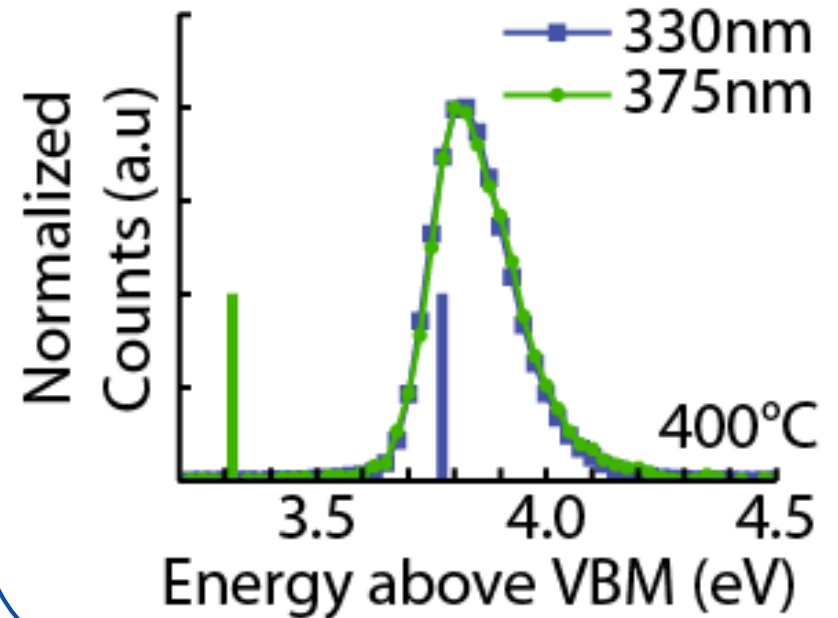
- **Photo-excite carriers into conduction band**
- **Thermionically emit these excited carriers**
- **Overcome electron affinity barrier (not full work-function)**
- **Collected at low work-function anode**

Photon-independent Emission Energy

- **Photon energy should not matter above band gap**
- **Very different from photoemission**
- **Green = just above gap**
- **Blue = well above gap, not above E_{vac}**



Energy distribution for different excitation energy



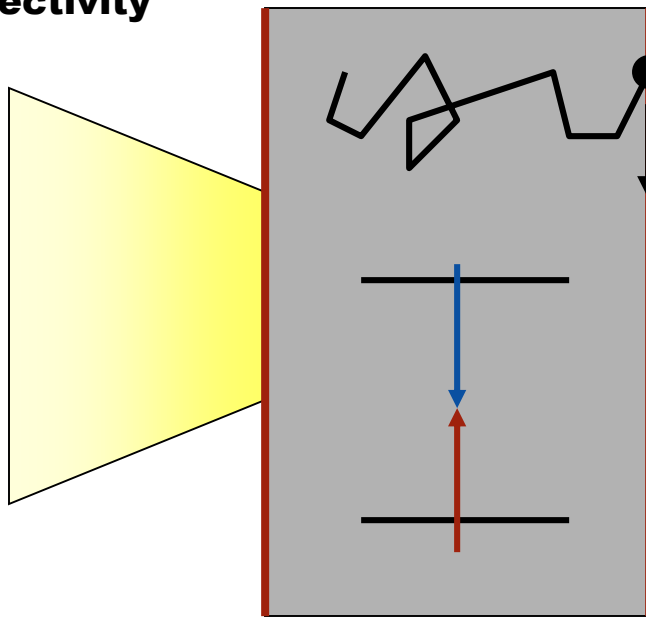
- **Identical energy distributions**
- **0.5 eV thermal voltage boost significant**
- **400C = 0.056 eV**
- **efficiency $\sim 10^{-4}$ - 10^{-5}**

Making PETE more efficient

Mechanisms that determine PETE efficiency:

• Incomplete absorption

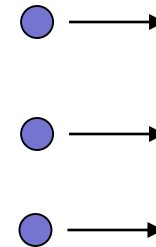
- thin films
- reflectivity



• Surface recombination

- defects
- coatings
- intrinsic surface

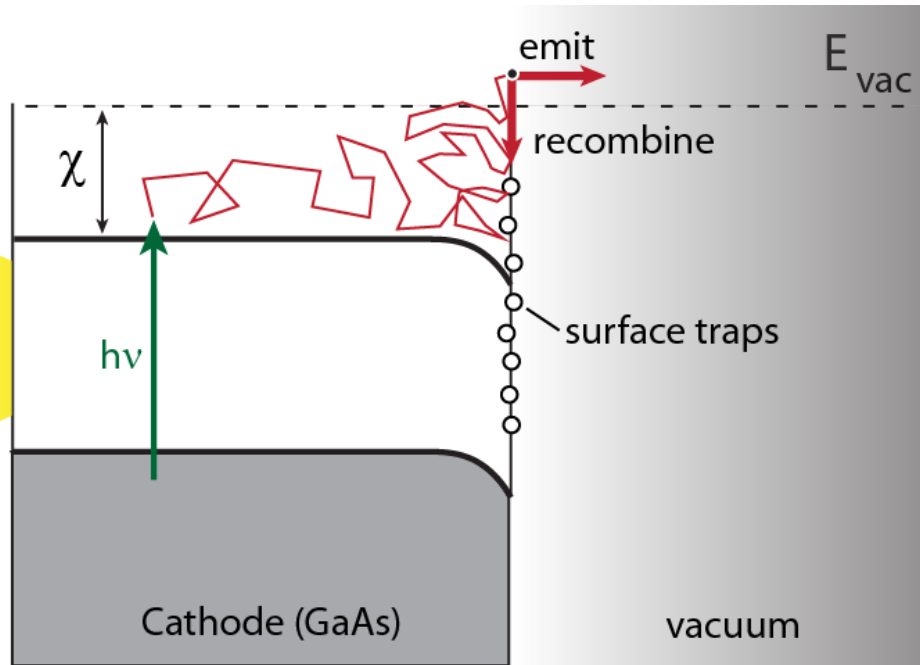
• Space Charge



• Bulk recombination

- black body
- auger
- defects

Reducing Surface Recombination

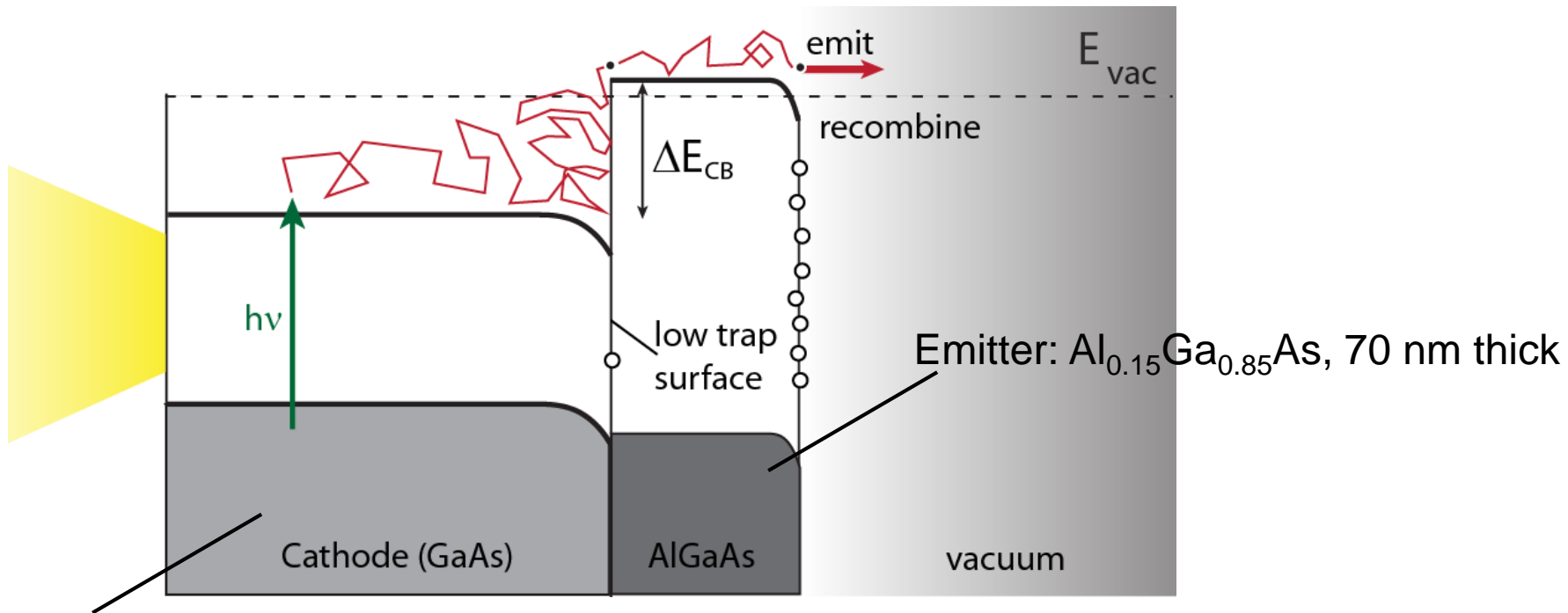


$$S_{surf} \sim 10^1 - 10^6 \text{ cm/s}$$

$$S_{emit} = \langle v_x \rangle e^{-\chi/kT}$$
$$\sim 10^1 - 10^5 \text{ cm/s}$$

- Front-surface recombination directly competes with emission
- Surface coatings (Cs, etc) increase recombination
- Can lower χ , but lose voltage
- High surface recombination in most cathode materials:
 - 10^6 cm/s in GaAs
 - Yield < 20% for $T < 300^\circ\text{C}$, $\chi = 200$ meV

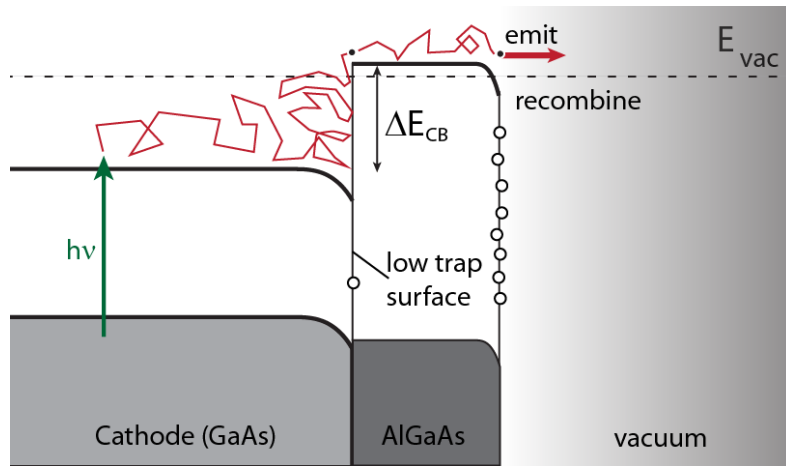
Heterostructure cathode for PETE



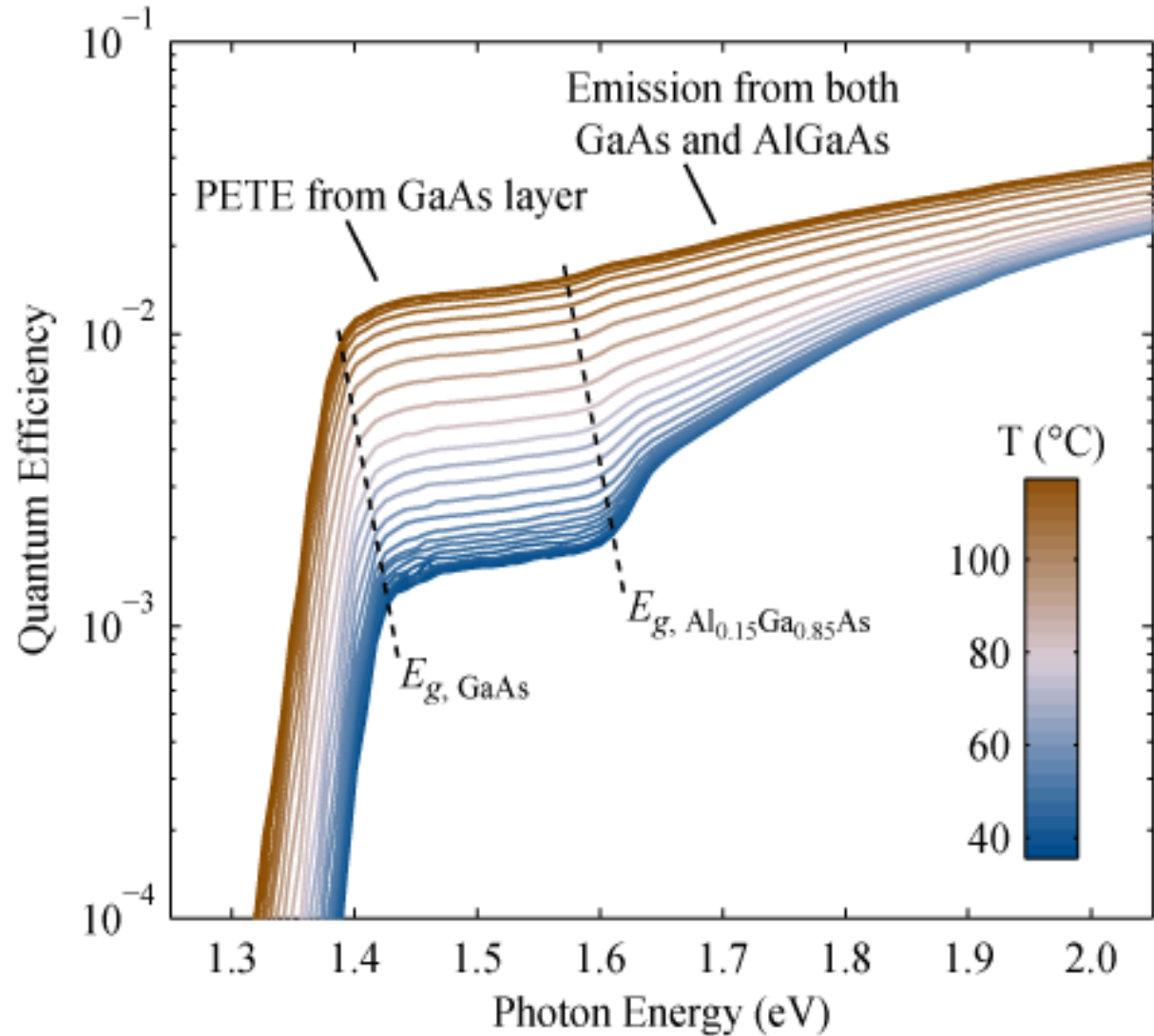
Absorber: GaAs, 1 μm thick

- Reduce recombination at surface by adding $\text{Al}_{0.15}\text{Ga}_{0.85}\text{As}$ layer
 - Very low recombination
 - Excellent control over barrier height
 - $\Delta E_{\text{CB}} \approx 220 \text{ meV}$, largely independent of temperature
- Coat front surface to be negative electron affinity
 - little sensitivity to surface recombination

Heterostructured cathode performance

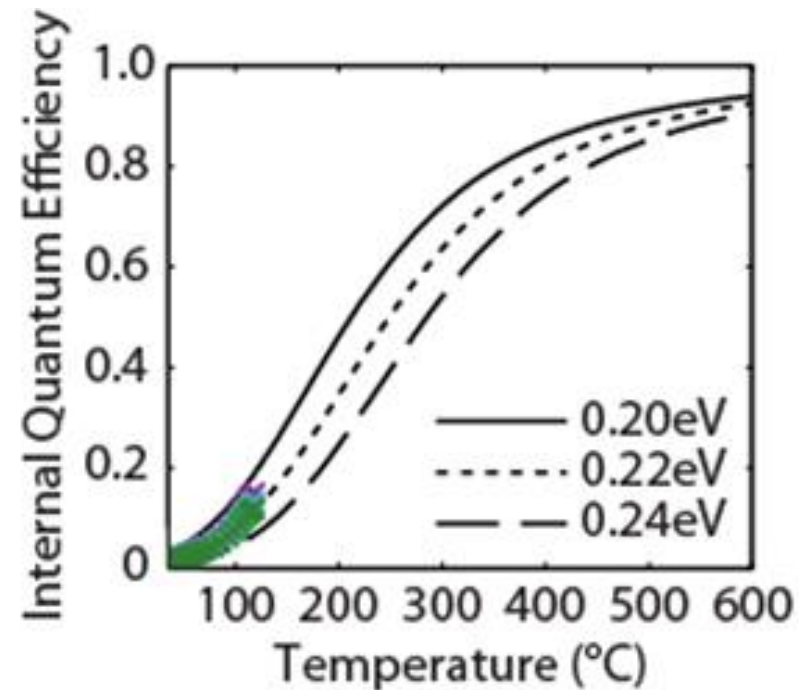
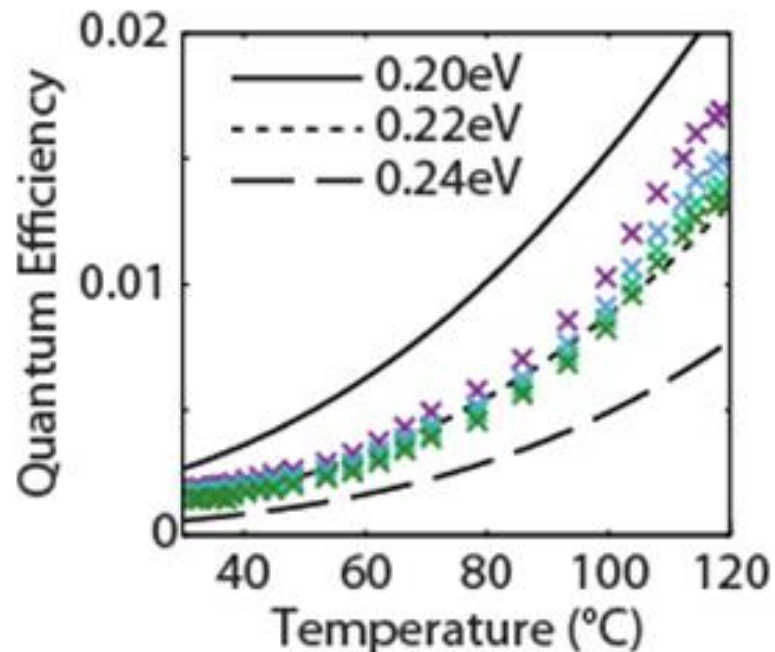


- **Very strong temperature dependence**
- **Yield increases 10x from 313 K to 393**
- **PETE current dominates photoemission from GaAs layer**
- **Limited by thermal stability of CsO coating**



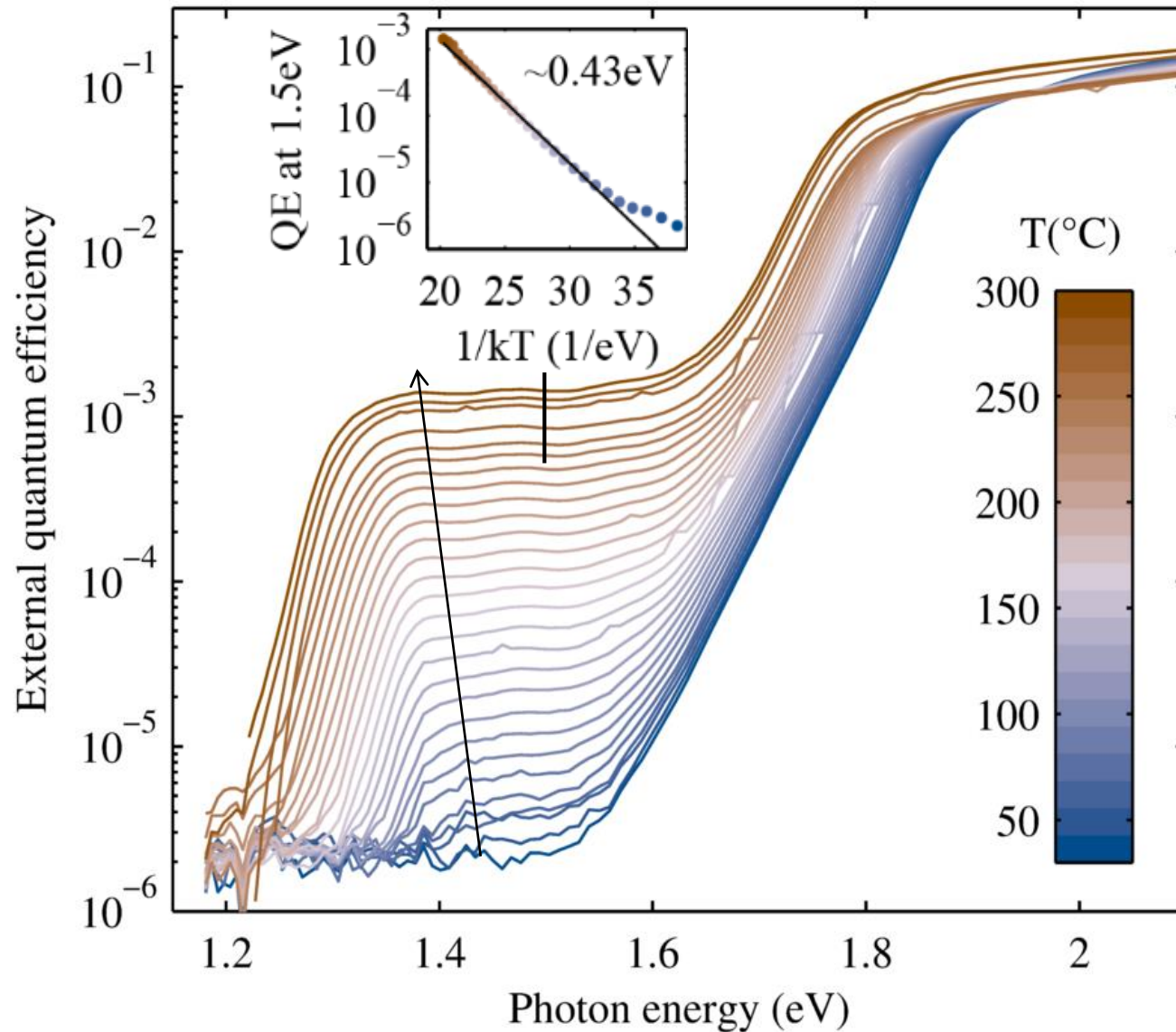
***Improved quantum yield
from 10^{-4} to 2.5%***

Tantalizing performance with Temperature



- **QY increases as calculated from RT to 120 C**
- **Sample surface degrades above 150C**
- **If we could get just to 400C with exactly these properties, would have >80% QY.**

“Solid-state” GaInP PETE device



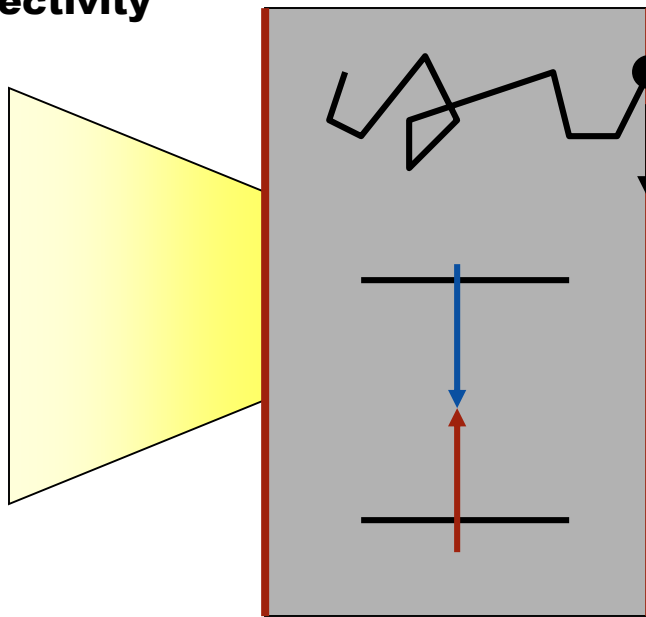
- Much larger temperature range is possible
- 1000x improvement in current

Making PETE more efficient

Mechanisms that determine PETE efficiency:

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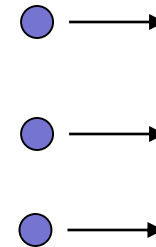
- thin films
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• Surface recombination

- defects
- coatings
- intrinsic surface

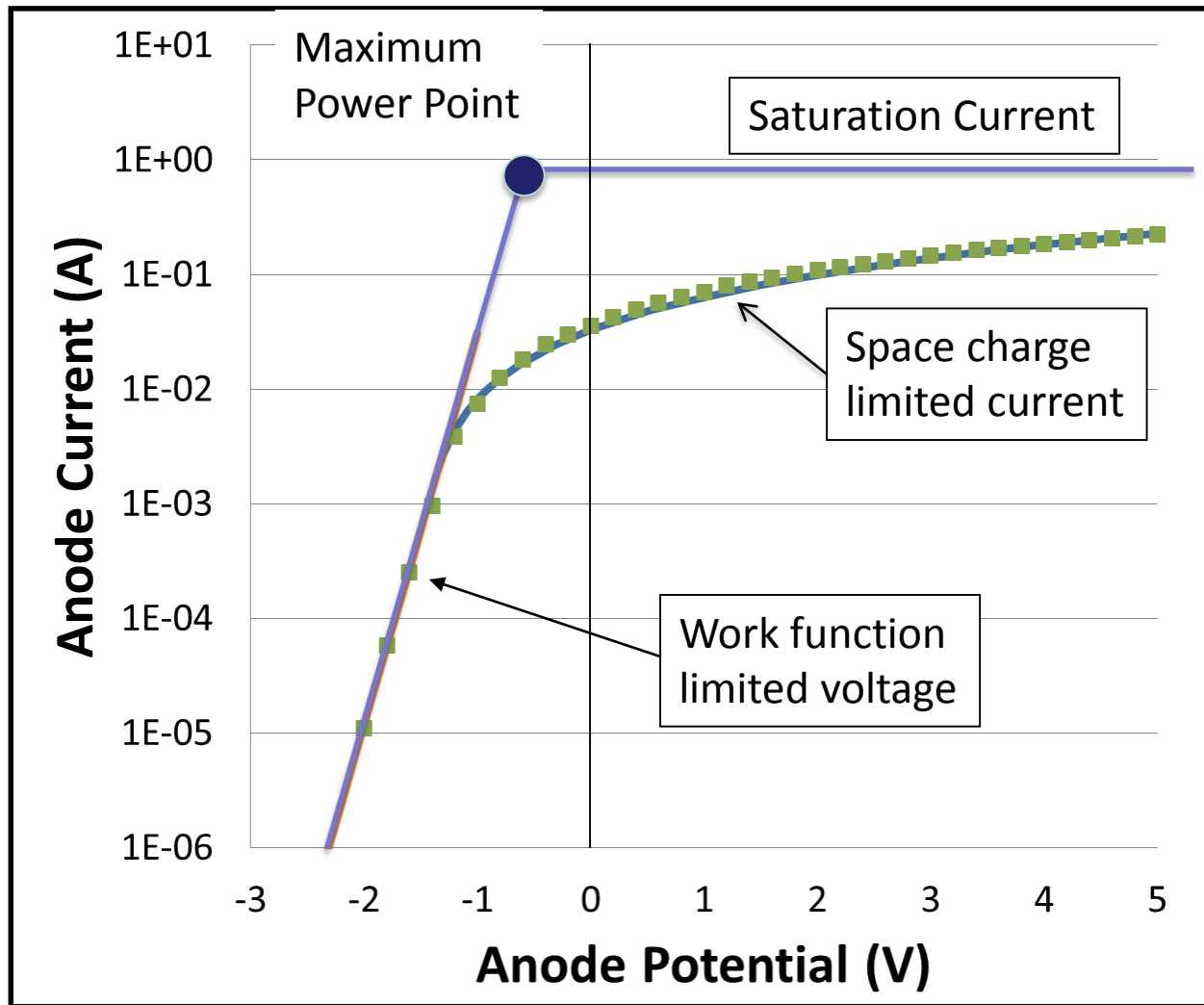
• Space Charge



• Bulk recombination

- black body
- auger
- defects

The Space Charge Limit



- At a given T, current saturates due to space charge:

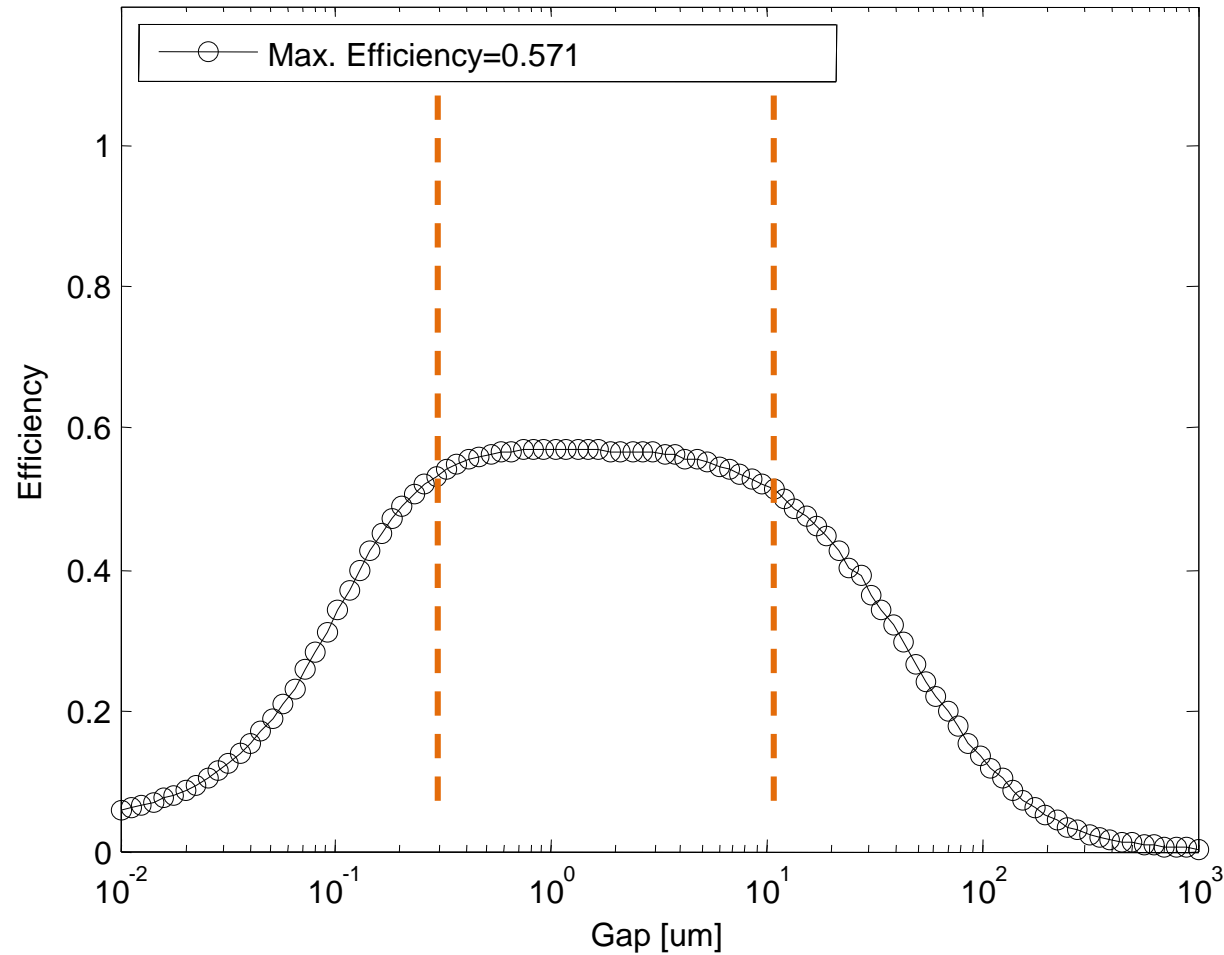
$$J = \frac{4\sqrt{2}}{9} \epsilon_0 \left(\frac{e}{m_e} \right)^{1/2} \frac{|V|^{3/2}}{d^2}$$

Child-Langmuir Law

- Depends on output voltage, electrode separation distance

- Power generation occurs at negative anode potentials

Optimal Gap Size



**Photon
tunneling**

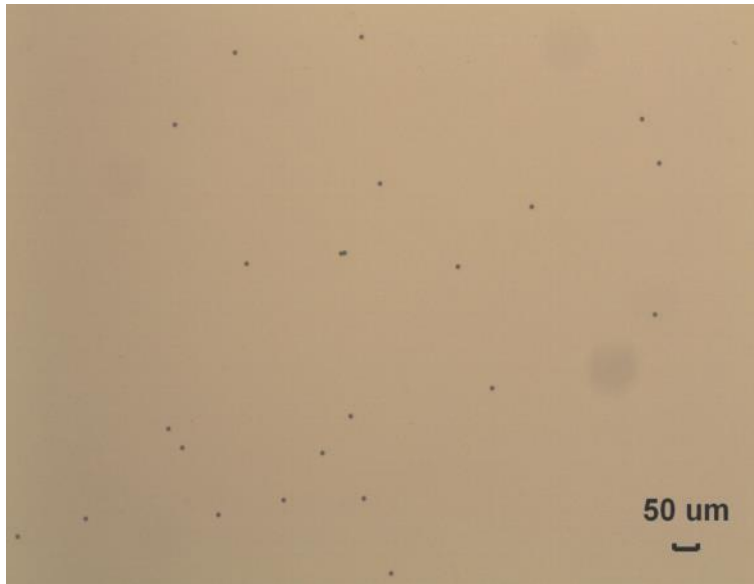
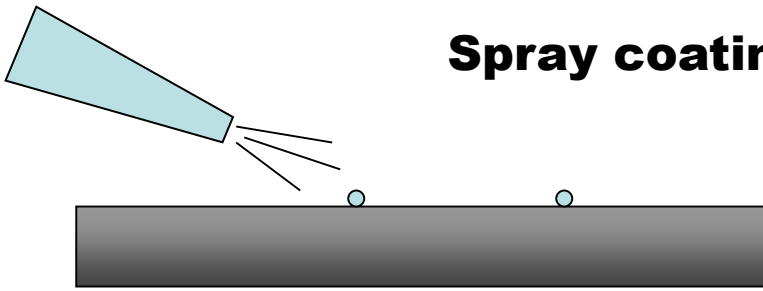
**Optimal Gap:
> 90% of Max.
Eff.**

**Space charge
limit**

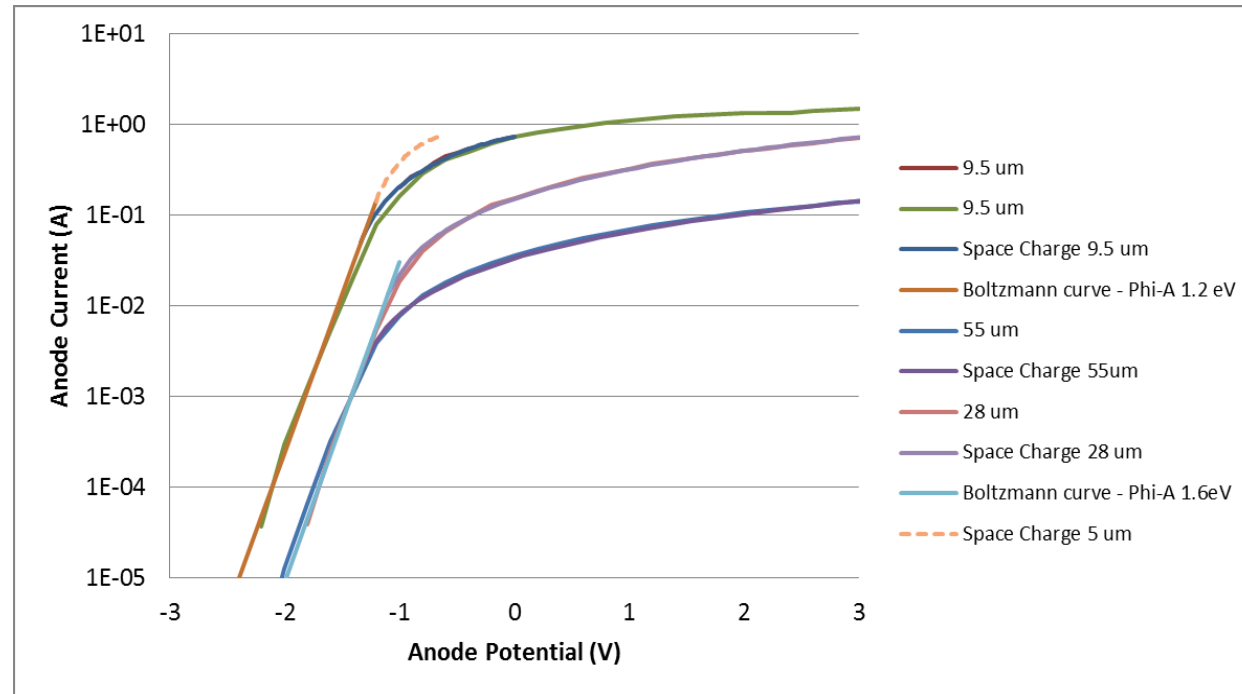
$$\underline{TE=2000[K], TC=300[K], \varphi_E = 3[eV], \varphi_C = 0.7[eV],}$$

MicroSphere Spacers

Spray coating



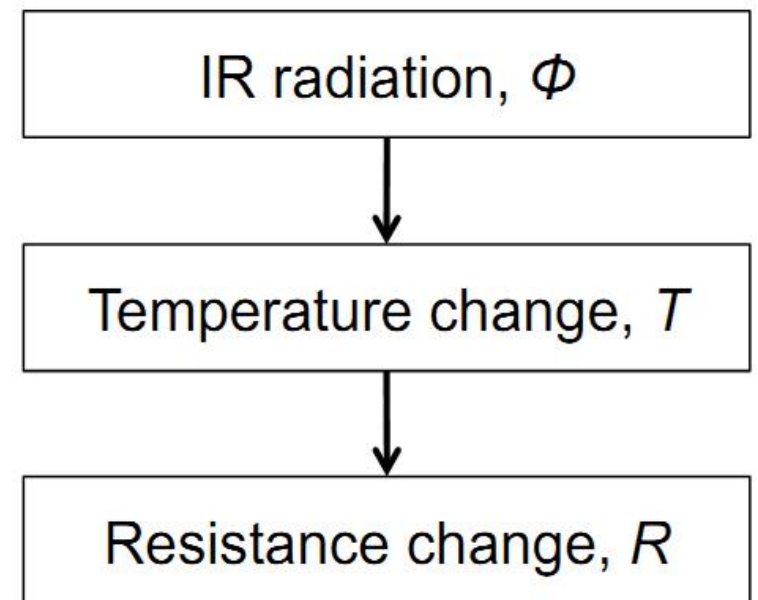
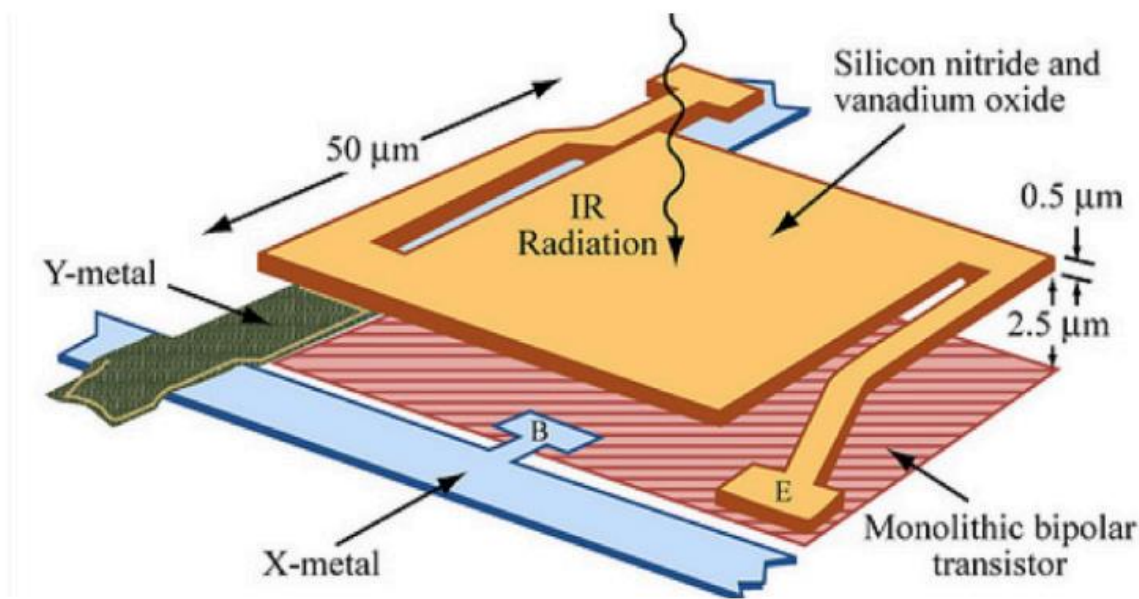
Low density 5 um
Microspheres



- Current is severely space charge limited at 55 um gap
- At 9.5 um gap, conversion efficiency of 1.8% at mpp
 - Does not account for heating losses, which are significant.
- Richardson constant 60-90 A/cm²K², $I_{mpp} > 1.5$ A/cm²
- 5 um gap model predicts x2 increase in current and efficiency

Micro-fabrication Approach

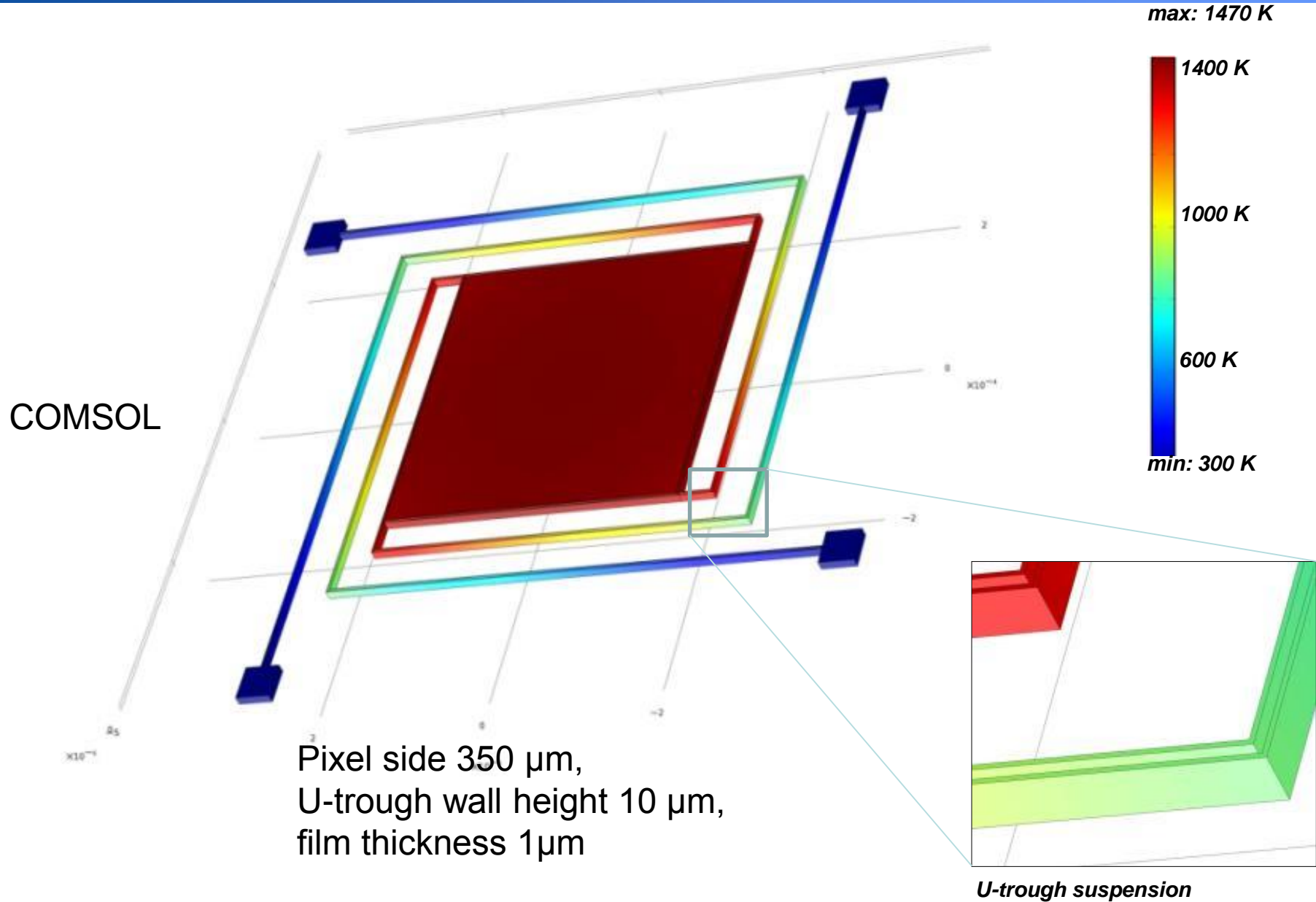
- Micro-bolometer arrays for uncooled IR imaging (Honeywell Research, 1980s – 1990s)



- > Temperature changes on the order of milli-K can be detected
- > Renewed interest for heads-up night vision for automobiles

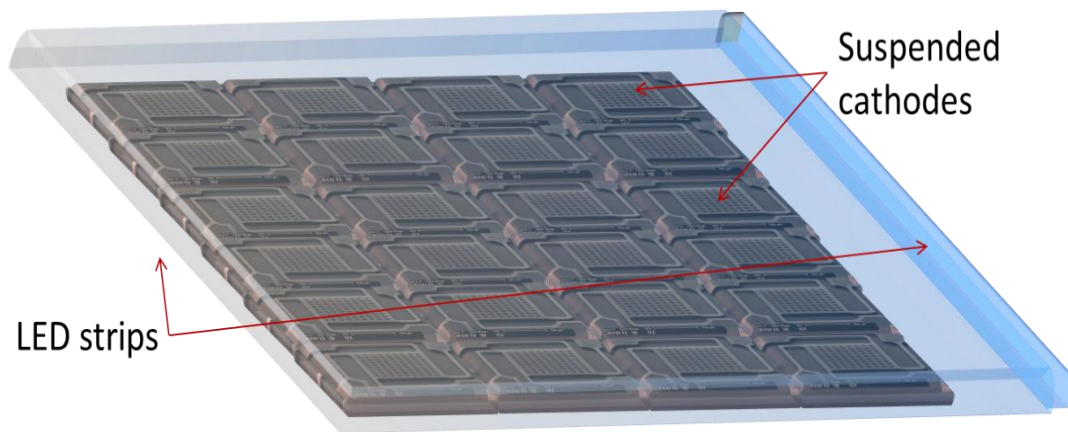
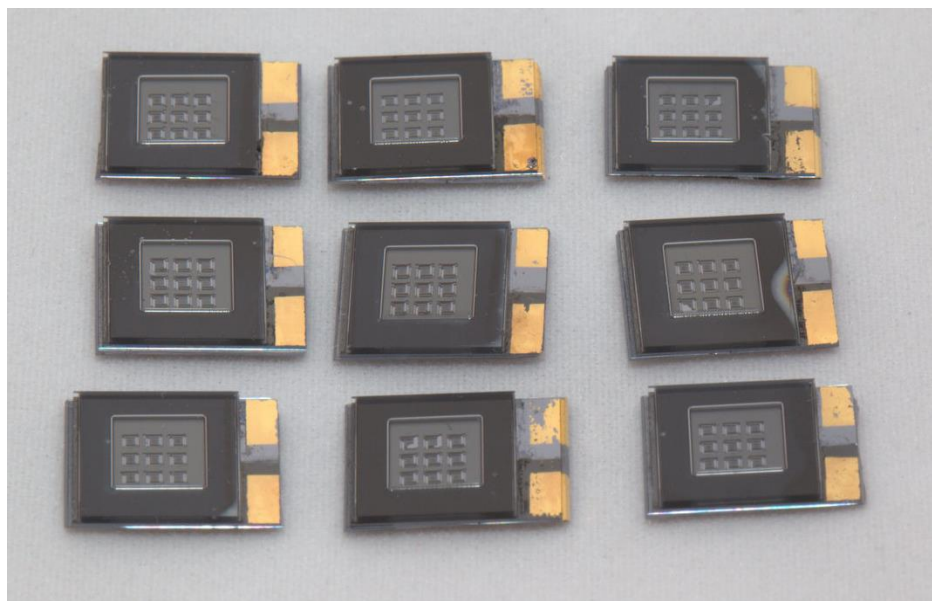
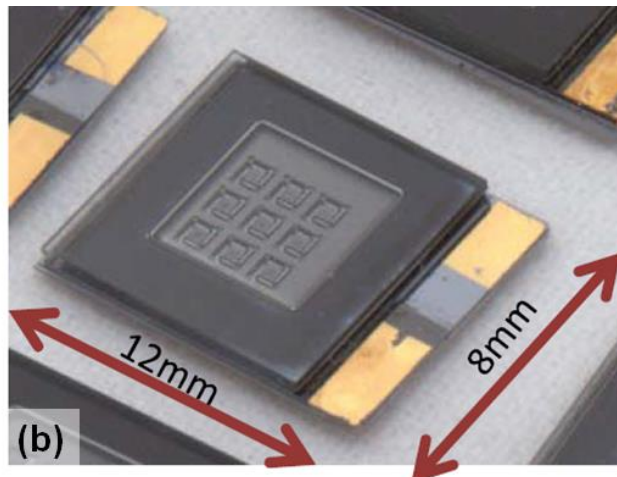
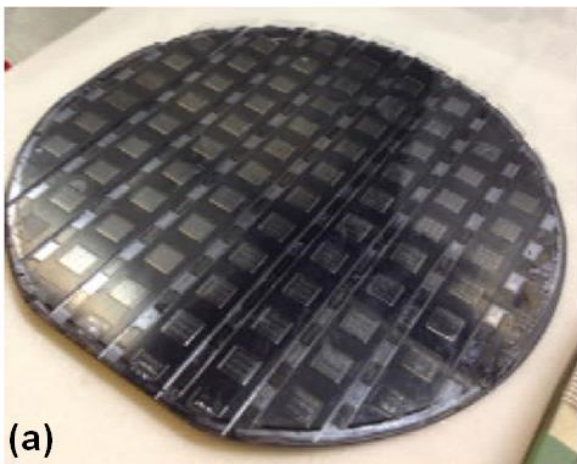
P. W. Kruse, *et al.*, *SPIE Proc.*, **3436**, 572-577 (1998).

Thermal Expansion and Isolation

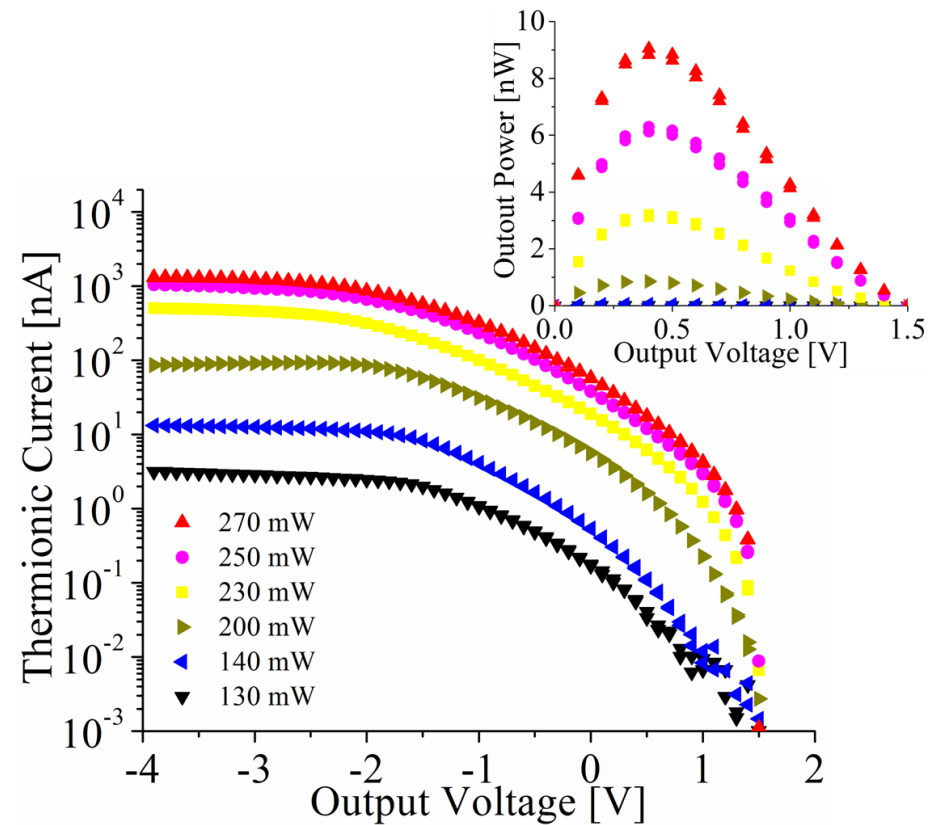
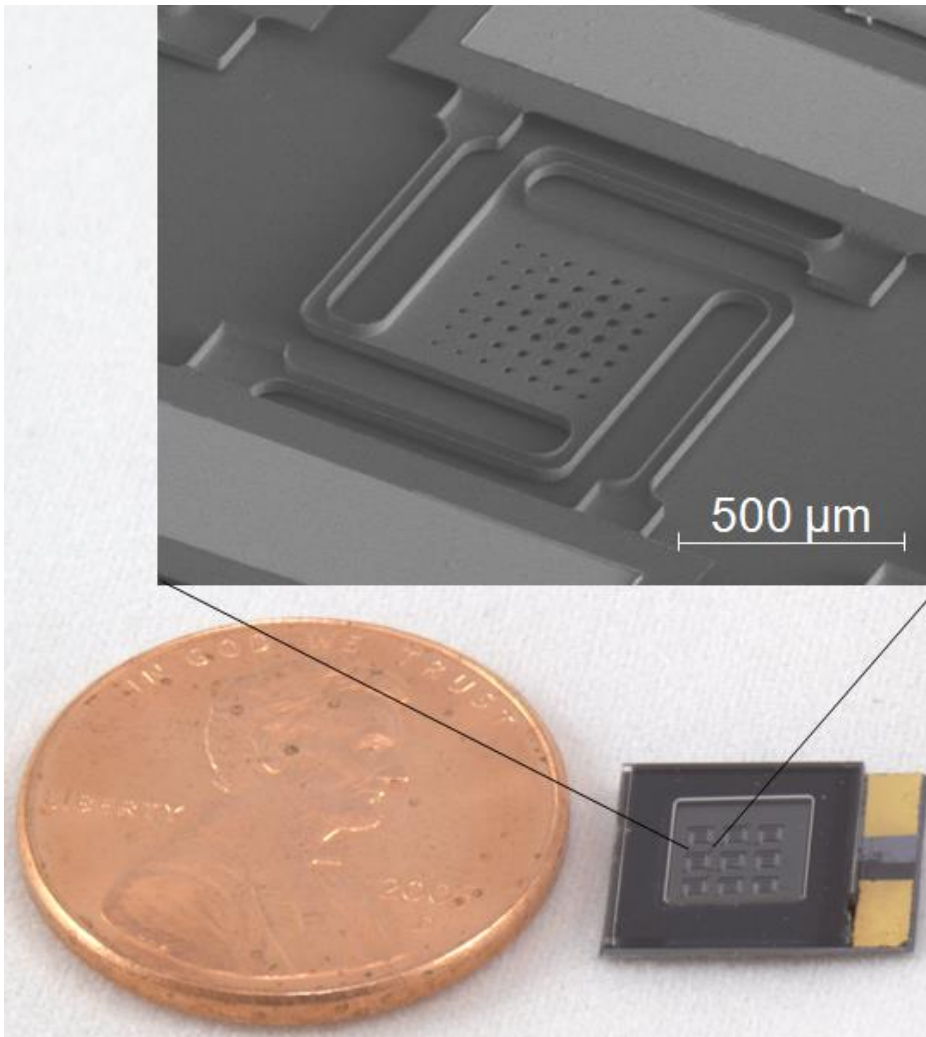


With I. Bargatin and R. T. Howe, unpublished

Vacuum-Encapsulated Micro-TECs



U-shape TEC



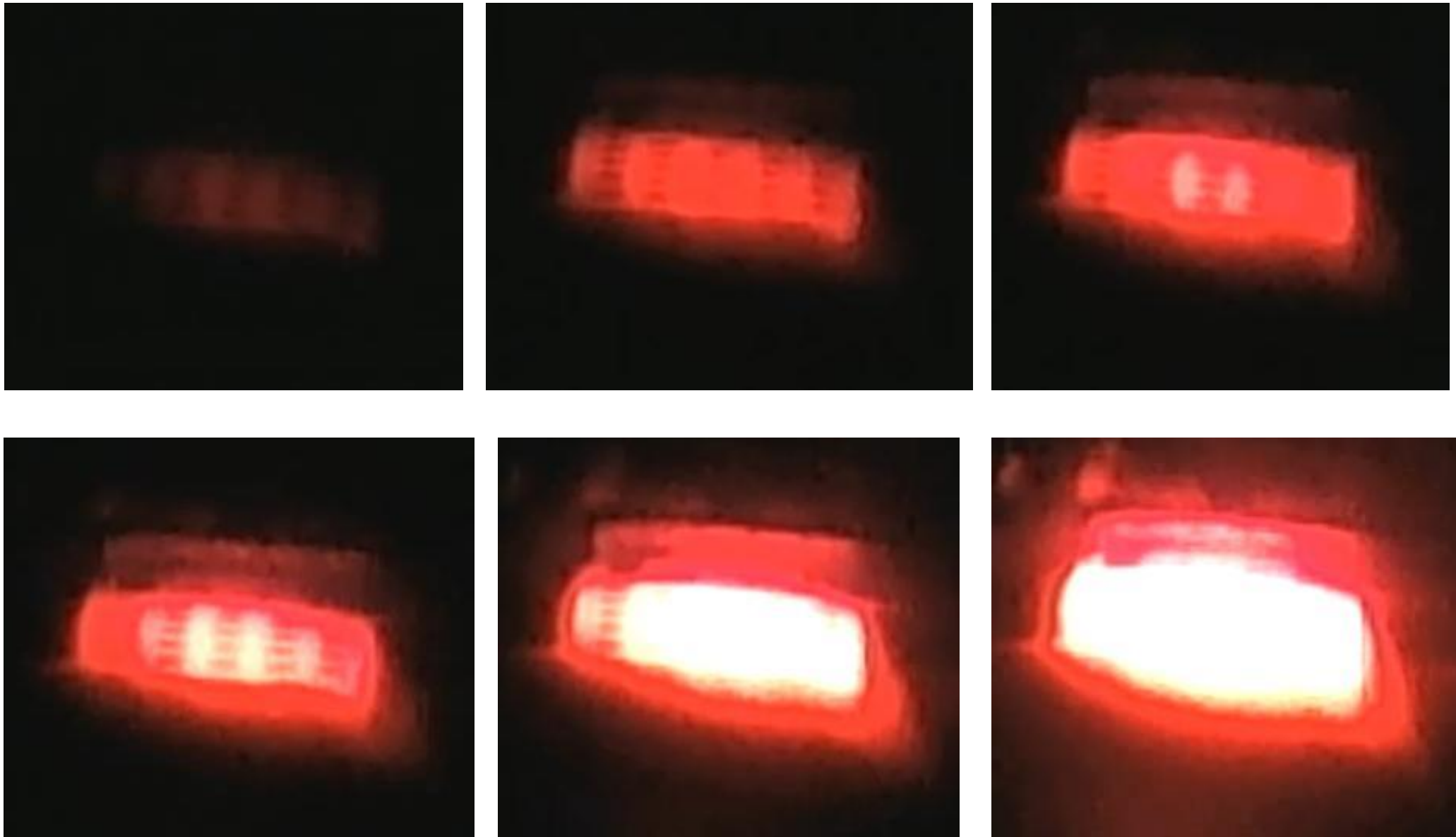
- **U-shaped devices on chip**
- **Anodically bonded encapsulation**
- **Prevents warping, shorting**
- **Current density up to 4 A/cm²**

“ENCAPSULATED THERMIONIC ENERGY CONVERTER WITH STIFFENED SUSPENSION”

Jae Hyung Lee¹, Igor Bargatin¹, Kentaro Iwami^{1,2}, Karl A. Littau¹, Maxime Vincent³, Roya Maboudian³, Z.-X. Shen¹, Nicholas A. Melosh¹, and Roger T. Howe¹

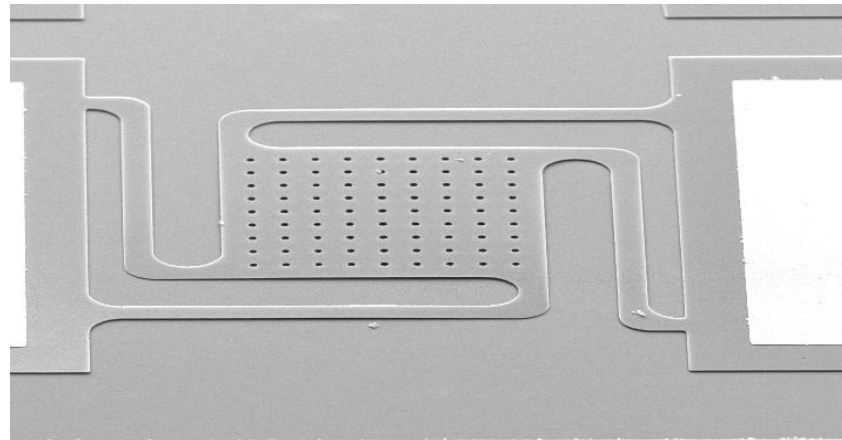
Hilton Head MEMS Workshop, 2012

Optical Heating of Poly-SiC Microcathode



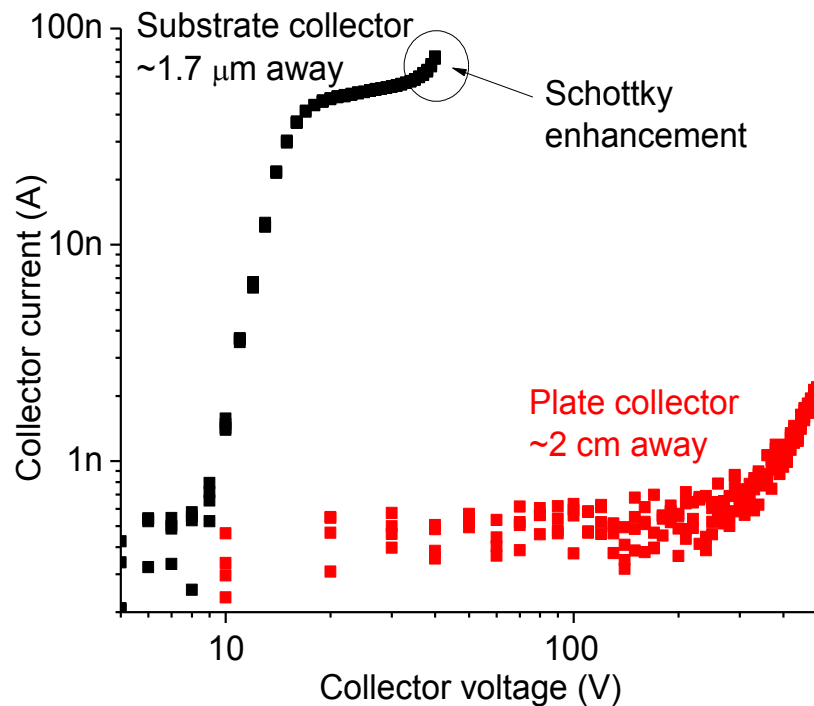
J.-H. Lee, *et al*, *IEEE MEMS 2012*, Paris, France.

Microfabricated SiC TEC device



Acc.V Spot Magn WD | 200 μ m
30.0 kV 3.0 100x 9.7

1.6 μ m gap

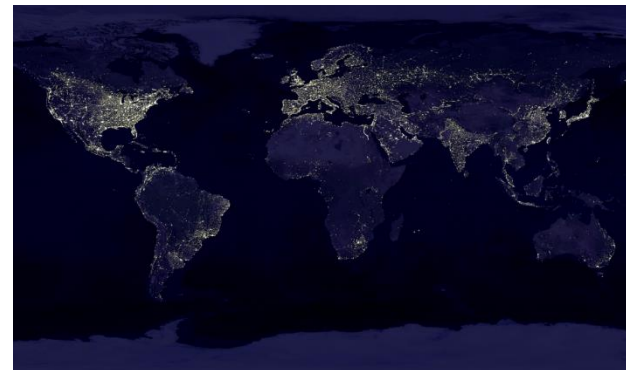
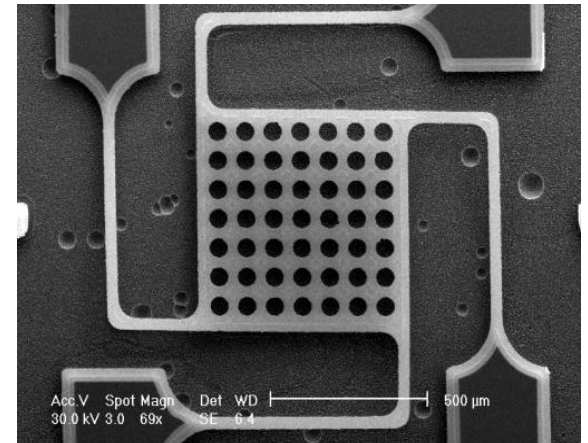
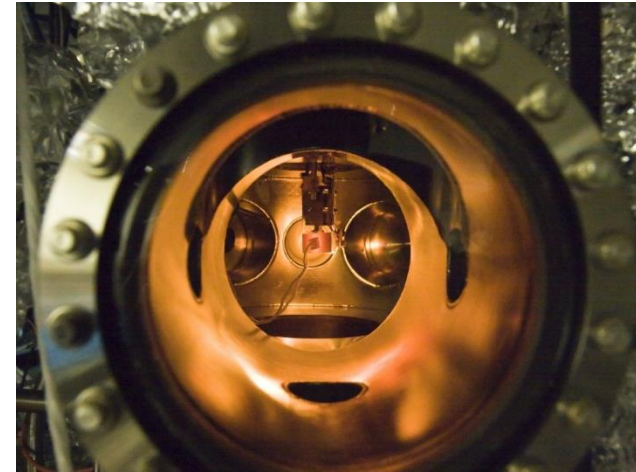


- 100x higher current
- Non-shorting
- Stable at high temperatures

Micro-scale spacing can largely mitigate space-charge issues

PETE Opportunities and Challenges

- **Surface recombination is an issue, but can be overcome**
- **Heterostructure design looks very promising**
- **Best results will be achieved by balancing thickness, electron affinity to recombination and emission rates**
- **Space charge can be lessened using beads for large devices, or microfabrication**



Acknowledgements

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Dr. Karl Littau



Collaborators:

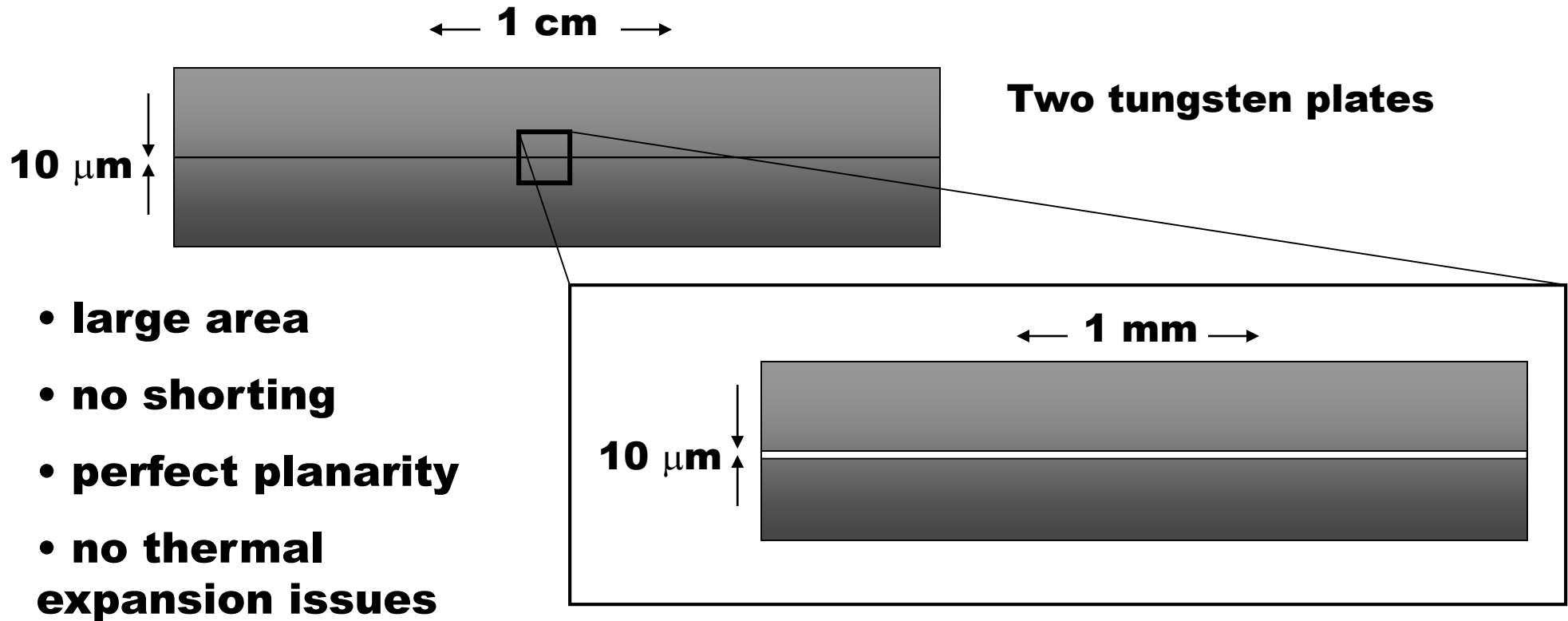
Prof. ZX Shen (Stanford Physics), Wanli Yang, Will Clay

Prof. Roger Howe (EE), Igor Bargatin, J Provine

Dr. Trevor Willey (LLNL)

Jeremy Dahl, Bob Carlson

Taking Thermionics below 100 μm

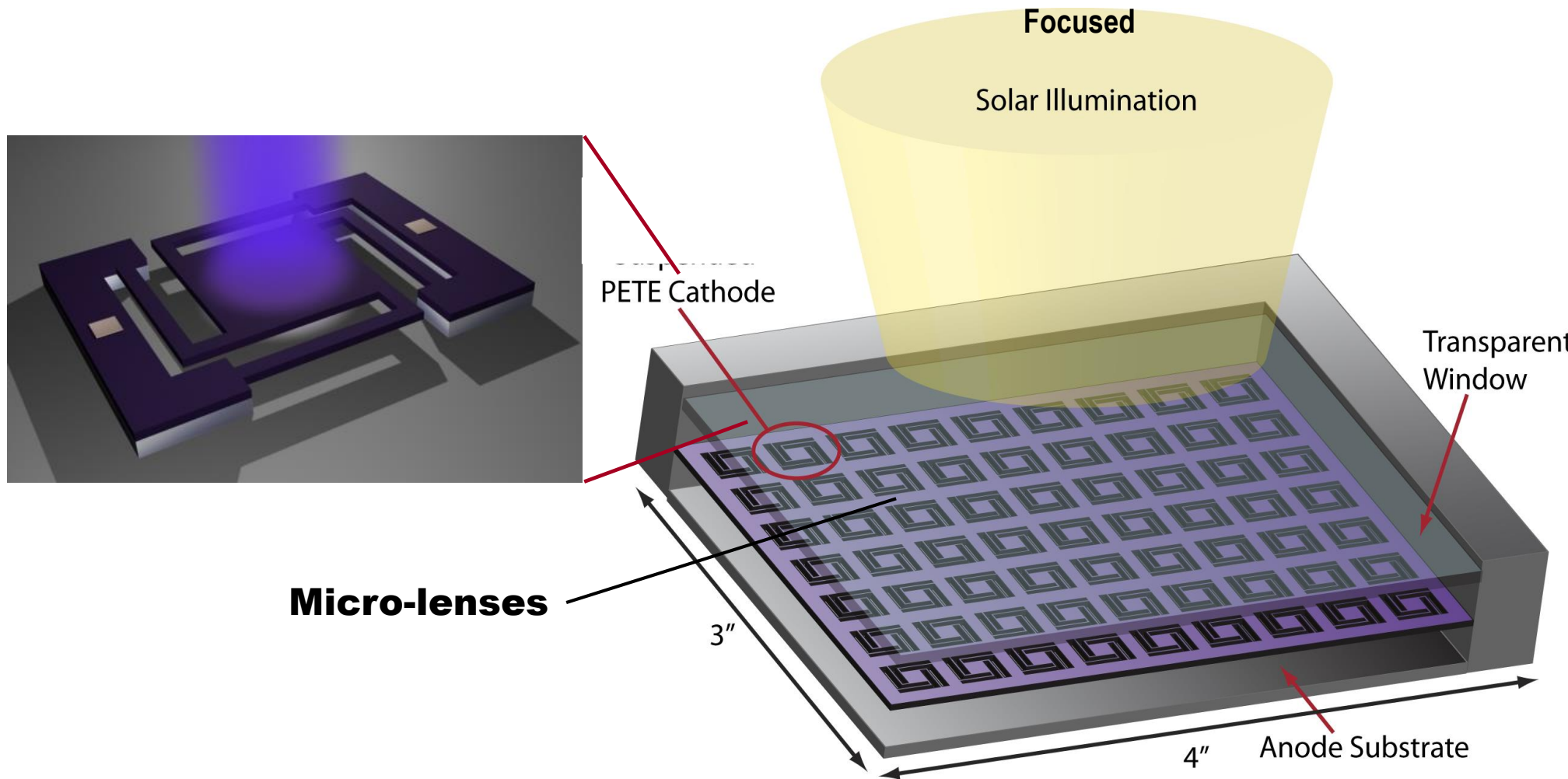


Simple Approach: Microbead Spacers



- simple, cheap
- low density by spraying
- poor thermal contact
- allows expansion

Small Scale Device Concept



- **Substrate functions as anode**
- **Vacuum encapsulation with a transparent lid**
- **Work-function lowering vapors in the cavity**

Solar Power Conversion

A lot of high-quality energy is available from the sun... how can we harvest it?



Solar Thermal (CSP)

- Converts sunlight into heat
- Concentrated solar thermal
- Uses well-known thermal conversion systems
- Efficiencies of 20-30%

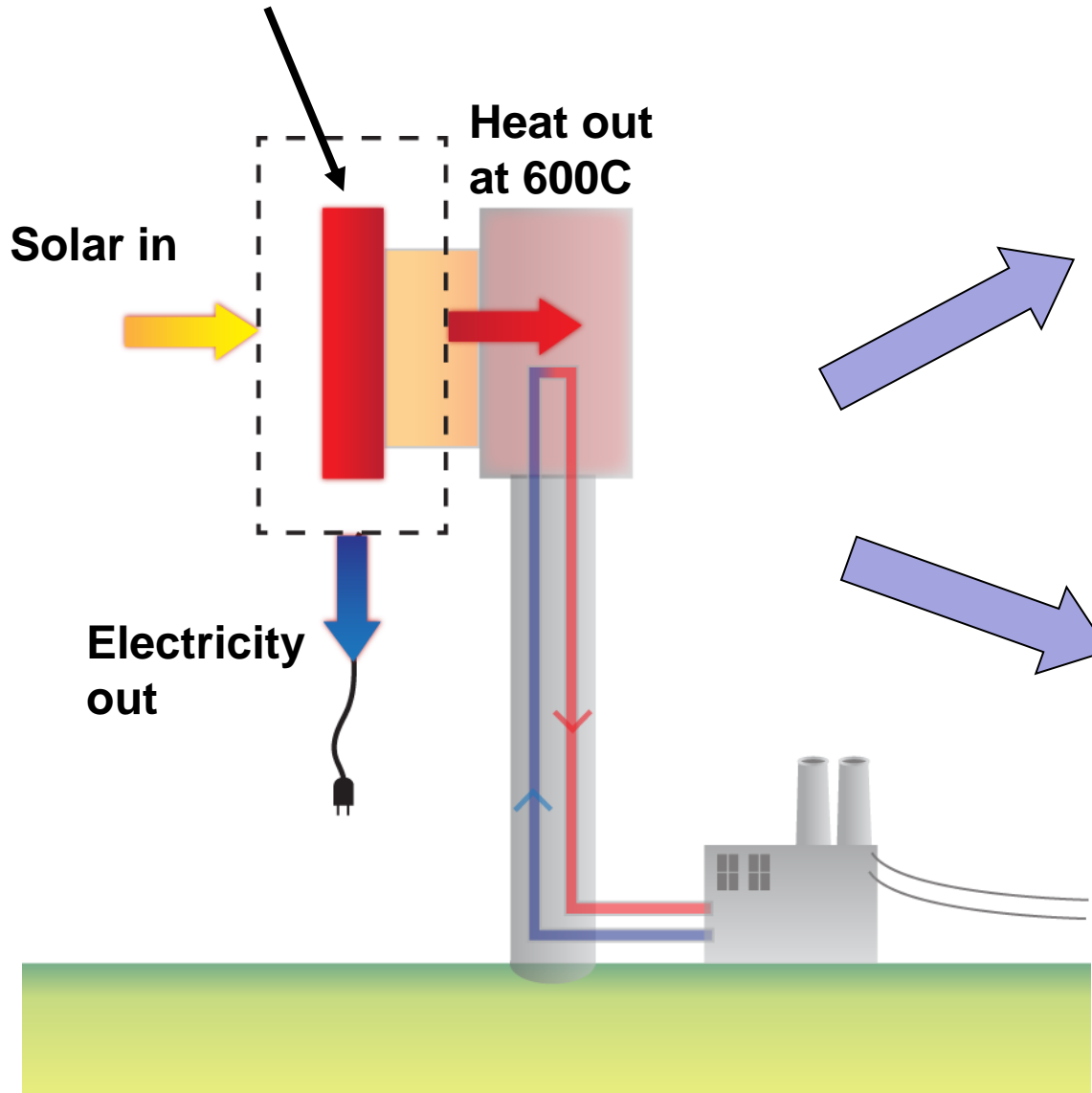


Photovoltaics (PV)

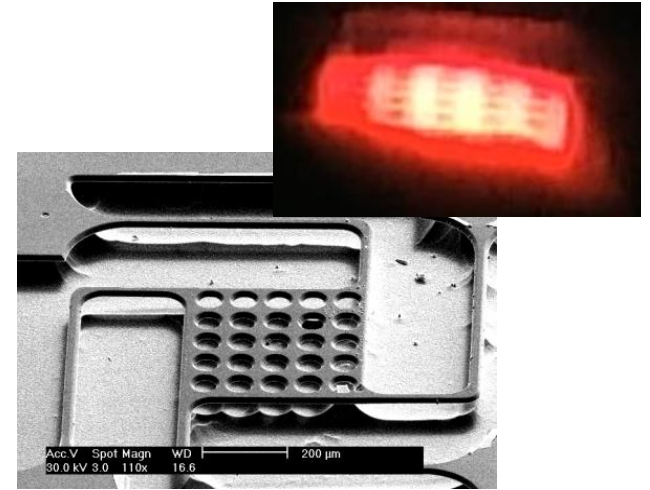
- collects fraction of incident energy
- “high grade” photon energy
- direct photon to electricity
- efficiencies 19-24% (single junction Si)

High Temperature Thermal Topping Cycles

What type of device?



Thermionic Emission



Photon-Enhanced Thermionic Emission

